

3D passive integration startup launches \$76M R&D program

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PARIS — Ipdia, the newly-formed startup that was once part of NXP BV's integrated passives device unit in Cote de Nacre, near Caen in Northwest France, has launched a R&D program for the development of ultra-miniaturized and high-performance silicon passive components.

Led by Ipdia, the four-year program represents a 53 million euro (\$76 million) investment from nine partners, namely Oseo, CEA-Leti, CNRS Laas, CNRS Crismat, 3D Plus, ELA Medical, Gemalto, Kalray and Movea.

The R&D program, dubbed PRIIM (Platform for the Realization of Shared Industrial Innovation) aims to define new application requirements for very high-growth markets such as implantable medical devices (stimulators, defibrillators, motion detectors), multimedia chips and complex embedded systems.

To achieve these goals, partners said they will work on new materials, structures and innovative processes to produce high-performance silicon passive components capable of withstanding severe environments and assembly technologies allowing ultra-miniaturization of future products.

Ipdia was formed in June 2009. Its creation results from more than ten years of R&D at Philips and NXP, which led to the invention of 3D technologies to integrate passive devices.

Ipdia's primary objective is to focus on two main axes: Integrated Devices for high brightness LEDs and Integrated Passive Devices for new markets such as medical, industrial, aerospace and defense.

Its "PICS" passive integration (IPD) technology is said to be a highly efficient way to integrate 10's to 100's of passive components such as resistors, capacitors, inductors and Zener Diode into a single silicon die.

The new company obtained a capital investment of more than 5 million euros (\$6.8 million) from a consortium of investors, including NXP. Ipdia is also purchasing some of the assets from the Cote de Nacre fab.